

Alpha & Omega Semiconductor Product Reliability Qualification Report

AOK080A60FDL rev A

Plastic Encapsulated Device

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This report delineates the product's quality and reliability test outcomes. Specific sample sizes undergo accelerated environmental tests, with corresponding electrical testing before and after each interval. Analysis of the conclusive electrical test results affirms the product's adherence to AOS quality and reliability standards in accordance with **JEDEC**. Reference to the existing qualification outcomes for similar products is warranted due to structural similarities. The released product will be classified by its process family and undergo regular monitoring to ensure continual enhancements in product quality.

Test Item	Test Condition	Duration Lots/SS		Number of Failures	Reference Standard	
HTGB High Temperature Gate Bias	150°C Vgs=100% of Vgsmax	1000 hrs	3 * 77	0/231	JESD22-A108	
HTRB High Temperature Reverse Bias	150°C Vds=100% of Vdsmax	1000 hrs	3 * 77	0/231	JESD22-A108	
HAST Highly Accelerated Stress Test	130°C, 85%RH, Vds = 80% of Vdsmax up to 42V	96 hrs	3 * 77	0/231	JESD22-A110	
H3TRB High Humidity High Temperature Reverse Bias	85°C, 85%RH, Vds = 80% of Vdsmax up to 100V	1000 hrs	3 * 77	0/231	JESD22-A101	
AC Autoclave	121°C, 100%RH, 15psig	96 hrs	3 * 77	0/231	JESD22-A102	
TC Temperature Cycling	-65°C to 150°C, air to air	1000 cycles	3 * 77	0/231	JESD22-A104	
IOL Intermittent Operational Life	∆Tj = 100°C t _{on} = 5 minutes t _{off} = 5 minutes	6000 cycles	3 * 77	0/231	MIL-STD-750 Method 1037	
ESD_HBM	Class 2 (2000V~3999V)		3 pcs	-	JS-001	
ESD_CDM	Class C3 (≥1000V)	-	3 pcs	-	JS-002	

I. Reliability Stress Test Summary and Results



FIT rate (per billion): 7.63 MTTF = 14960 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

At 60% Confidence Level **Failure Rate** = $Chi^2 \times 10^9 / [2 (N) (H) (Af)] = 7.63$ **MTTF** = $10^9 / FIT = 14960$ years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval **N** = Total Number of units from burn-in tests **H** = Duration of burn-in testing **Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and T_J u = 55°C) Acceleration Factor [**Af**] = **Exp** [Ea / k (1/T_J u - 1/T_J s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

T_J s = Stressed junction temperature in degree (Kelvin), K = C + 273.16

 $T_J u$ =The use junction temperature in degree (Kelvin), K = C + 273.16

 \mathbf{k} = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K